

Process: HB10C05-III

0.8um High Speed BiCMOS

Key Features

Bipolar(NPN, Vertical PNP, LPNP)

Maximum Operating Voltage 10V

Contact Size 0.8um

f_T max NPN/ VNP 8.0GHz / 5.5GHz @ $V_{ce}=1V$

f_{max} NPN/ VNP 5.5GHz / 4.0GHz @ $V_{ce}=1V$

CMOS

Operating Voltage 5.0V (5.5V Max.)

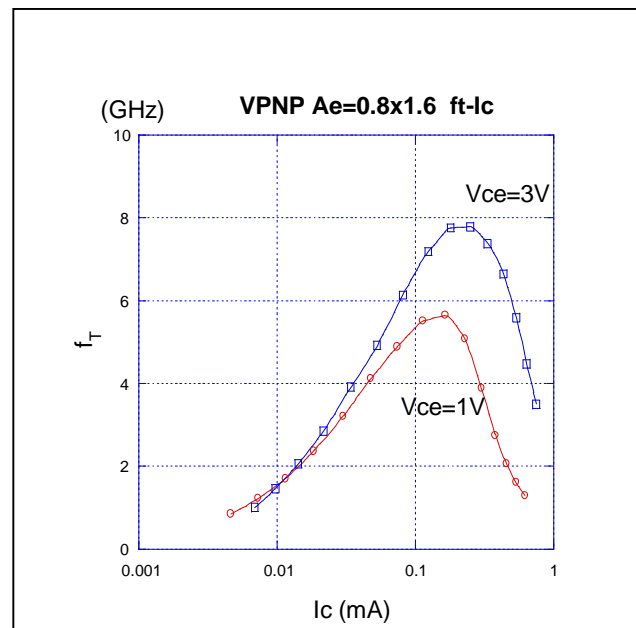
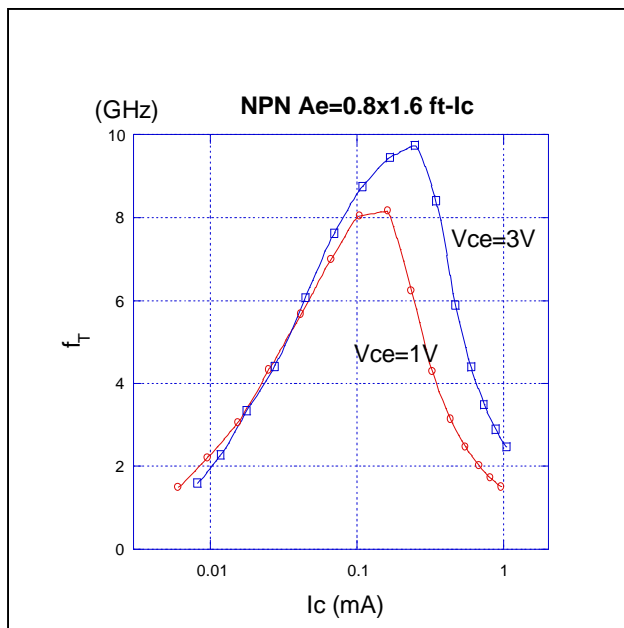
Min. Gate Length 0.8um

Capacitor

MIM · MOS

Resistor

Poly · Base · HR



Process: HB10C05-IV

Dielectrically-isolated High Speed BiCMOS

Key Features

Bipolar(NPN, Vertical PNP, LPNP)

Maximum Operating Voltage 10V

Contact Size 0.8 μ m

f_t max NPN/ VPNP 8.0GHz / 6.0GHz @ $V_{ce}=1V$

f_{max} NPN/ VPNP 7.0GHz / 6.0GHz @ $V_{ce}=1V$

No Parasitic Device

CMOS

Operating Voltage 5.0V (5.5V Max.)

Min. Gate Length 0.8 μ m

Capacitor

MIM · MOS

Resistor

Poly · Base · HR

